

SANYO	No.3261A	2SB1232/2SD1842
		2SB1232 : PNP Epitaxial Planar Silicon Transistor 2SD1842 : NPN Triple Diffused Planar Silicon Transistor 100V/40A Switching Applications

Features

- Large current capacity and wide ASO.
- Low saturation voltage.

Applications

- Motor drivers, relay drivers, converters, and other general high-current switching applications

() : 2SB1232

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V _{CB0}	(-)110	V
Collector-to-Emitter Voltage	V _{CEO}	(-)100	V
Emitter-to-Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)40	A
Collector Current(Pulse)	I _{CP}	(-)65	A
Base Current	I _B	(-)12	A
Collector Dissipation	P _C	3.0	W
		150	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	- 55 to + 150	°C

T_c = 25°C

Electrical Characteristics at Ta = 25°C

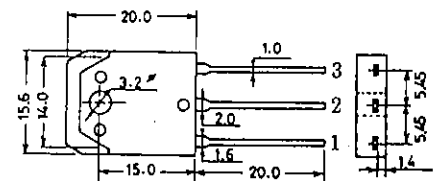
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = (-)100V, I _E = 0			(-)0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)5V, I _C = 0			(-)0.1	mA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)4A	50※		140※	
	h _{FE} (2)	V _{CE} = (-)2V, I _C = (-)16A	20			
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)16A, I _B = (-)1.6A			(-)0.8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = (-)16A, I _B = (-)1.6A			(-)1.5	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = (-)1mA, I _E = 0	(-)110			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = (-)5mA, R _{BE} = ∞	(-)100			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = (-)1mA, I _C = 0	(-)6			V

※ : For the h_{FE}(1) of the 2SB1232/2SD1842, specify at least two ranks in principle.

50 P 100	70 Q 140
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Package Dimensions 2022A

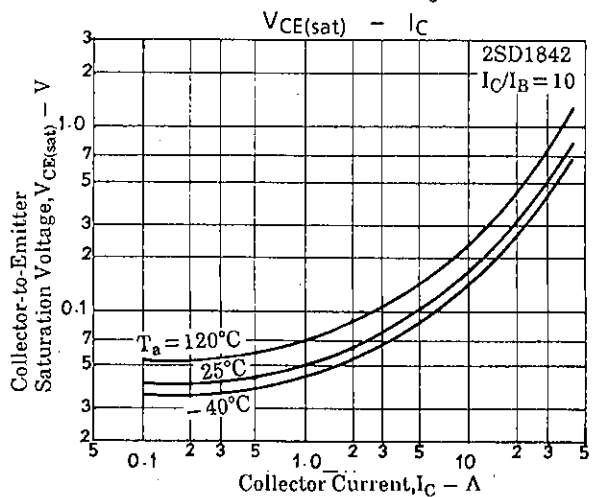
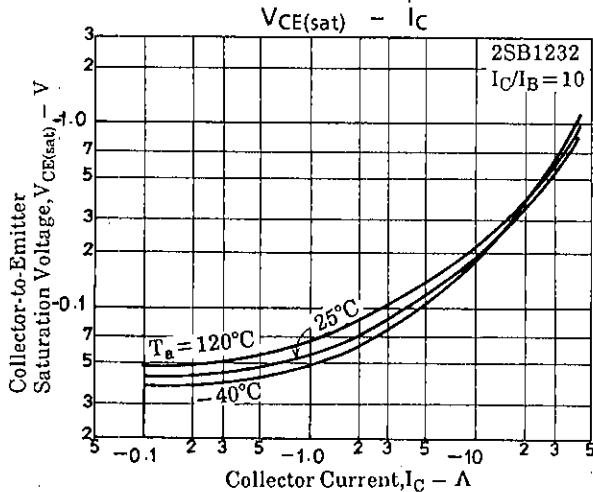
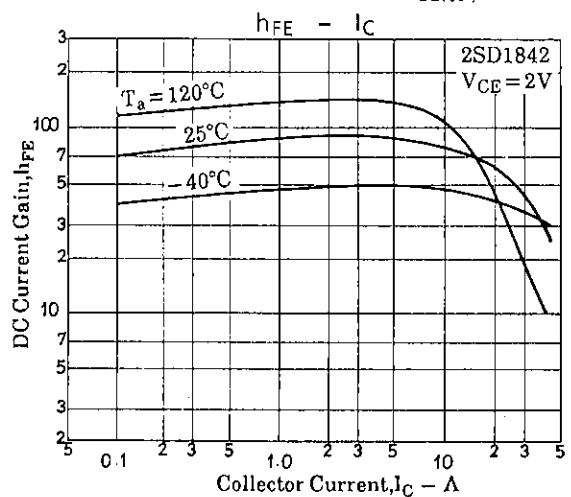
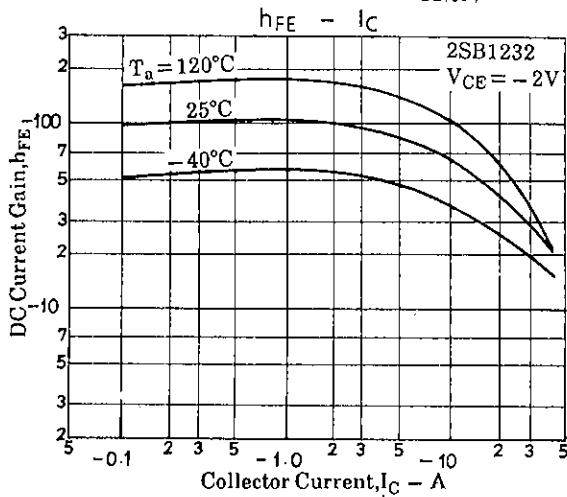
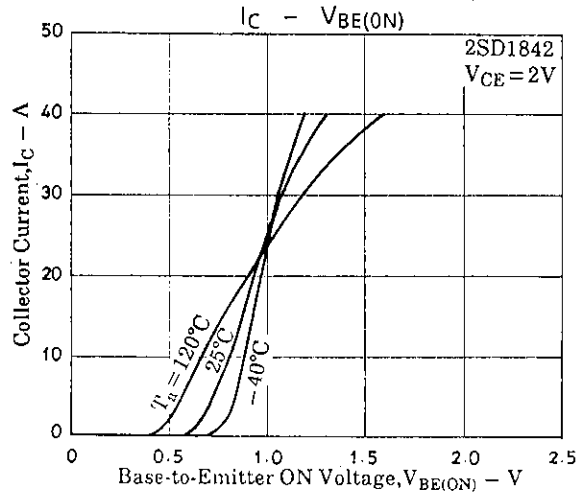
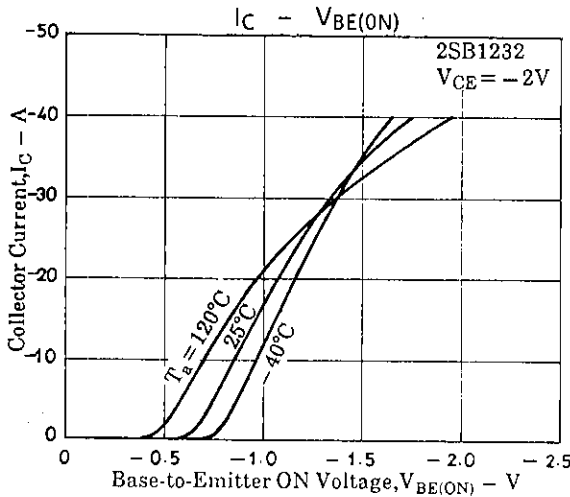
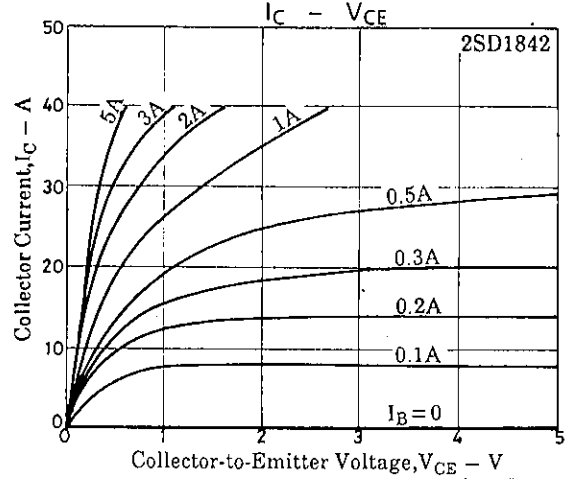
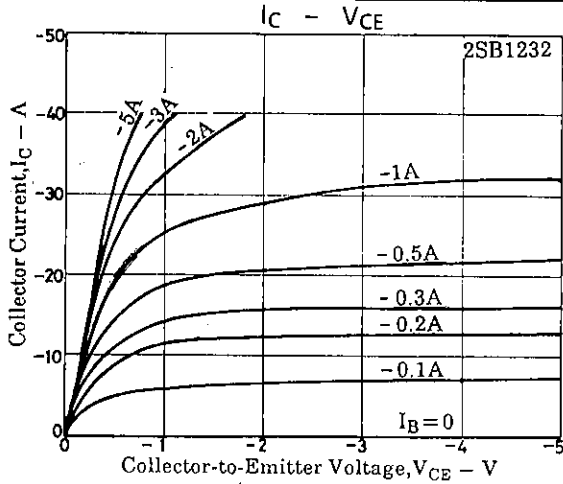
(unit : mm)



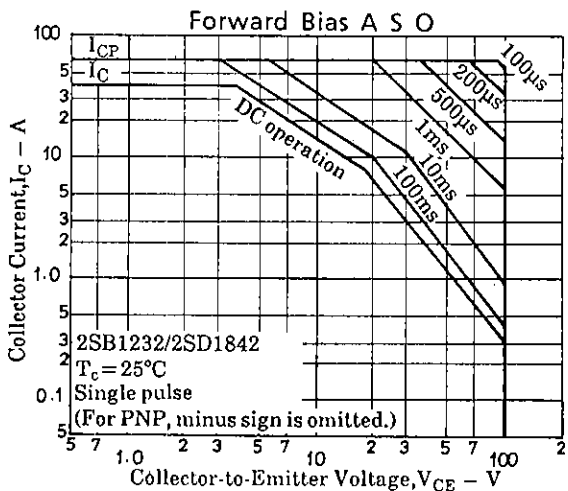
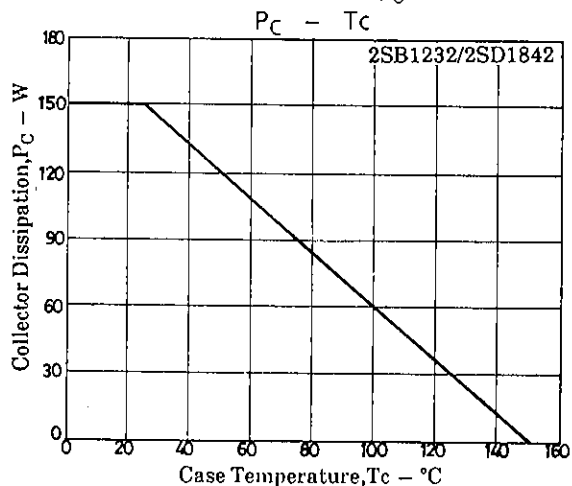
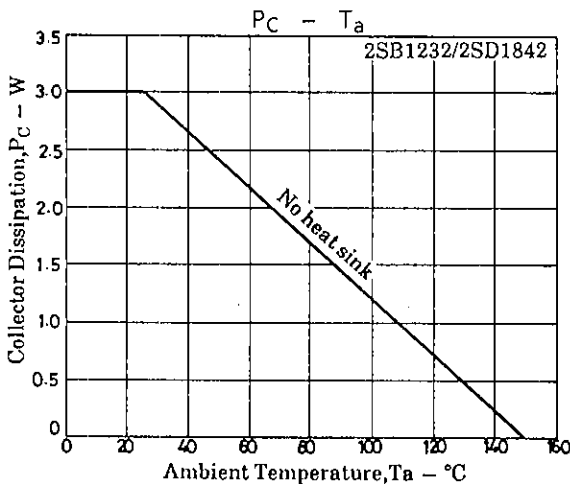
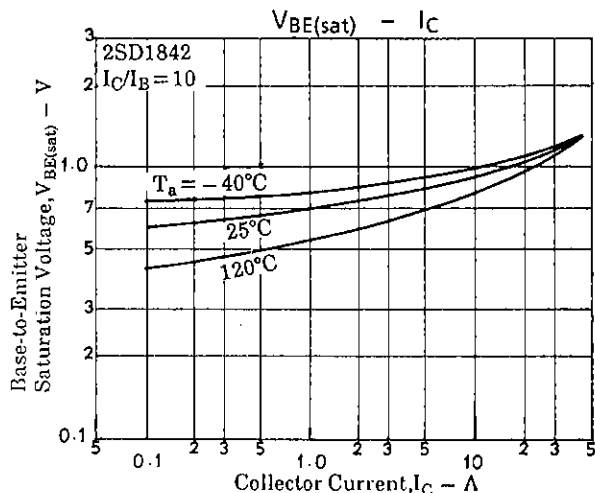
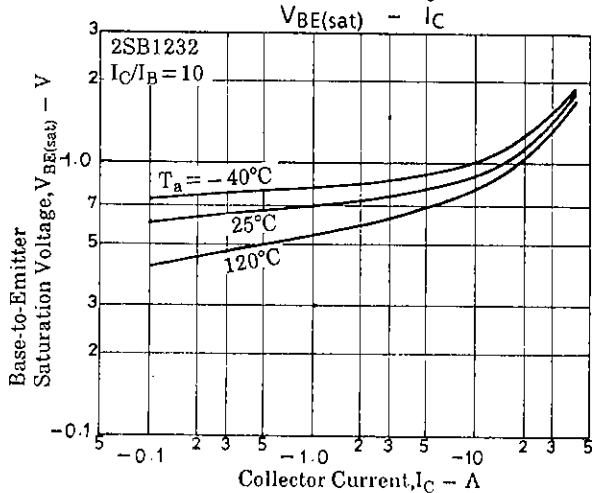
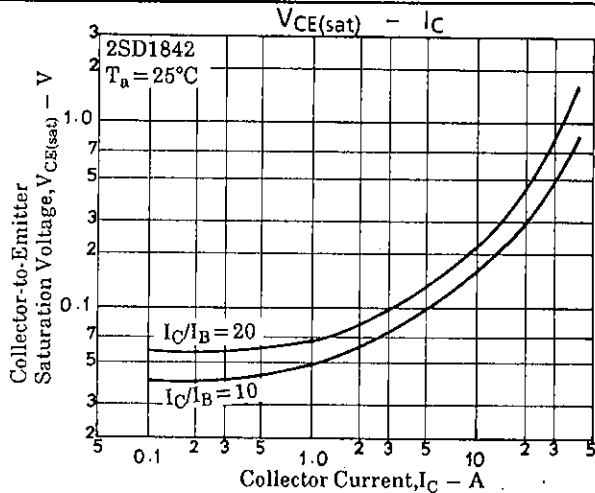
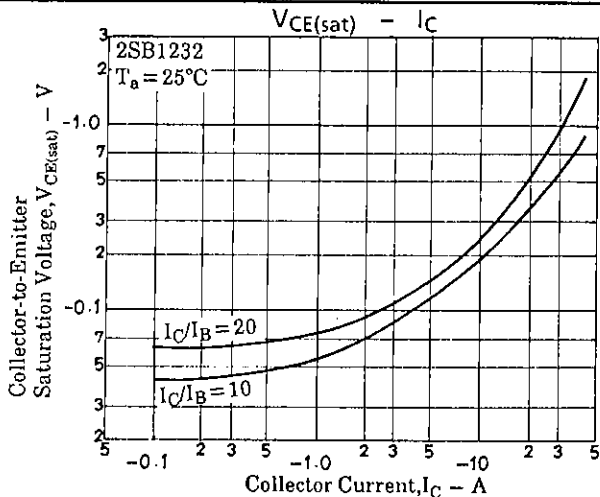
1 : Base
2 : Collector
3 : Emitter

SANYO: TO3PB

2SB1232/2SD1842



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